



# BUKNS1R4-40MYX8

40 V, 1.41 mΩ, Standard Level N-channel MOSFET in  
MLPAK56-WF

Rev. 1 — 29 July 2026

Product data sheet

## 1. General Description

BUKNS1R4-40MYX8 is an automotive N-channel MOSFET using T2-40 low-ohmic split-gate technology, housed in an MLPAK56 (SOT8038) package. This product is fully designed and qualified to meet AEC-Q101 requirements delivering high performance and reliability.

## 2. Features and Benefits

AEC-Q101 automotive qualification:

175 °C rating suitable for thermally demanding automotive environments

T2-40 split-gate trench technology:

Reduced cell-pitch enables enhanced power density resulting in lower conduction losses in same footprint

MLPAK micro-leads with side-wettable flanks:

Proven board-level reliability during thermal cycling

Visual (AOI) soldering inspection, no need for expensive X-ray equipment

Easy solder wetting for good mechanical solder joint

MLPAK copper-clip technology:

Improved reliability with reduced  $R_{th}$ ,  $R_{DS(on)}$ , and package inductance

Increases maximum current capability and improves current spreading

## 3. Applications

- 12 V and 24 V automotive systems
- Motor, lighting, and solenoid control
- Ultra high-performance power switching

## 4. Quick Reference Data

Table 1. Quick Reference Data

| Symbol                  | Parameter                        | Conditions                                                                                                                                       | Min  | Typ  | Max  | Unit |
|-------------------------|----------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------|------|------|------|------|
| $V_{DS}$                | drain-source voltage             | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                                                                                       | -    | -    | 40   | V    |
| $I_D$                   | drain current                    | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2 [1]</a>                                                                    | -    | -    | 190  | A    |
| Static Characteristics  |                                  |                                                                                                                                                  |      |      |      |      |
| $R_{DS(on)}$            | drain-source on-state resistance | $V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>                                                    | 0.67 | 1.23 | 1.41 | mΩ   |
| Dynamic Characteristics |                                  |                                                                                                                                                  |      |      |      |      |
| $Q_{G(tot)}$            | total gate charge                | $I_D = 25\text{ A}$ ; $V_{DS} = 32\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a> | -    | 55   | 66   | nC   |

[1] Application tests show a continuous current of 190 A. The PCB, the thermal design, and the operating temperature limit the actual current.

5. Pinning Information

Table 2. Pinning Information

| Pin | Symbol | Description | Simplified Outline | Graphic Symbol |
|-----|--------|-------------|--------------------|----------------|
| 1   | S      | source      |                    |                |
| 2   | S      | source      |                    |                |
| 3   | S      | source      |                    |                |
| 4   | G      | gate        |                    |                |
| 5   | D      | drain       |                    |                |
| 6   | D      | drain       |                    |                |
| 7   | D      | drain       |                    |                |
| 8   | D      | drain       |                    |                |

6. Ordering Information

Table 3. Ordering information

| Type number     | Package |                                                                                                                                                    |           |
|-----------------|---------|----------------------------------------------------------------------------------------------------------------------------------------------------|-----------|
|                 | Name    | Description                                                                                                                                        | Version   |
| BUKNS1R4-40MYX8 | MLPAK56 | Plastic, thermal enhanced surface mounted package with side-wettable flanks (SWF); minileads; 8 terminals; pitch 1.27 mm; 5.6 × 5.15 × 1.0 mm body | SOT8038-4 |

7. Marking

Table 4. Marking Codes

| Type Number     | Marking Code    |
|-----------------|-----------------|
| BUKNS1R4-40MYX8 | BN1S404<br>X8MY |

8. Limiting Values

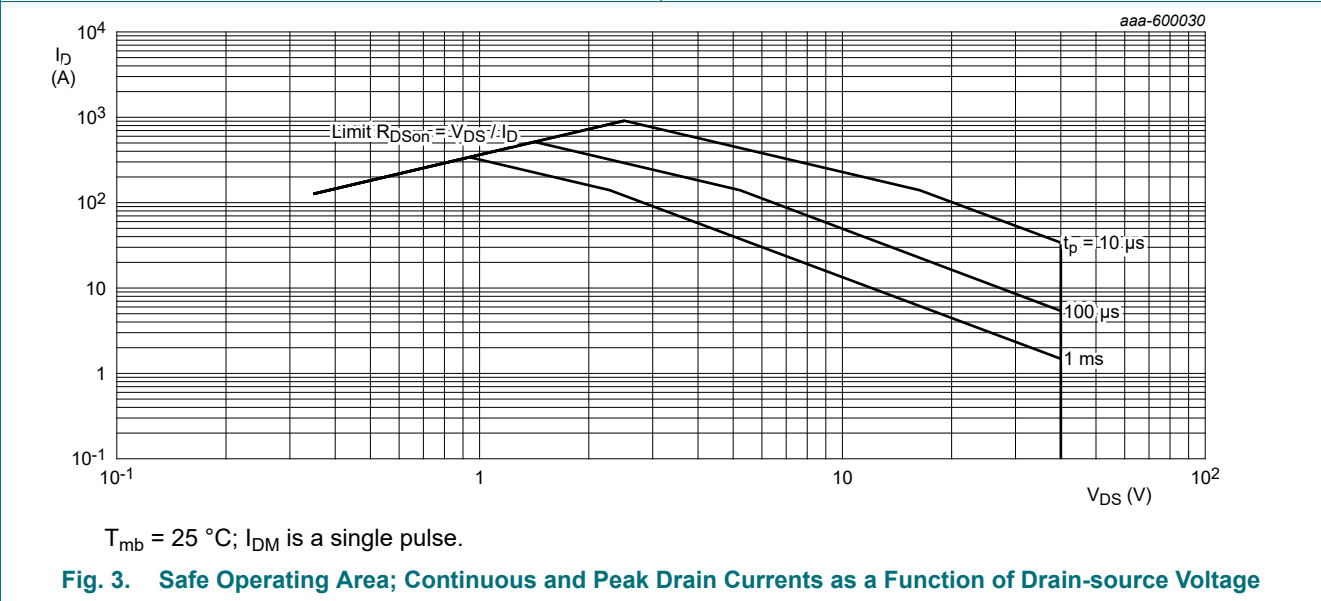
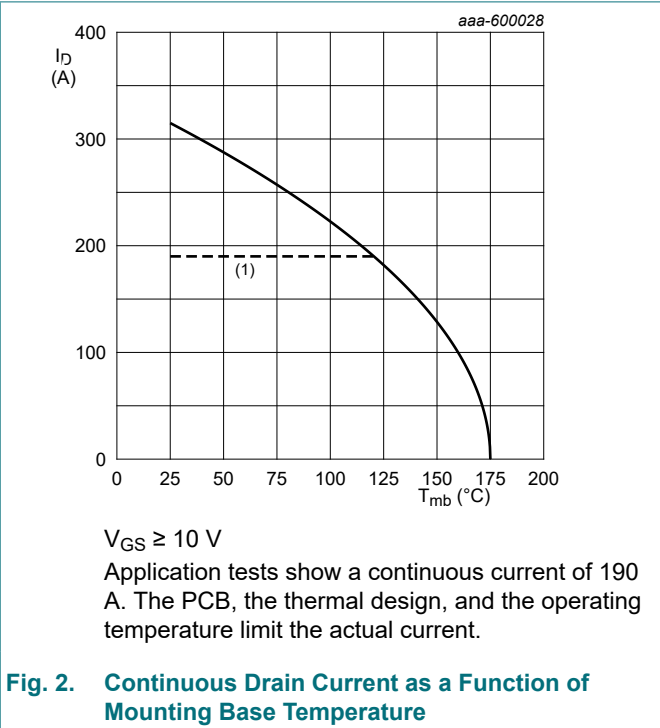
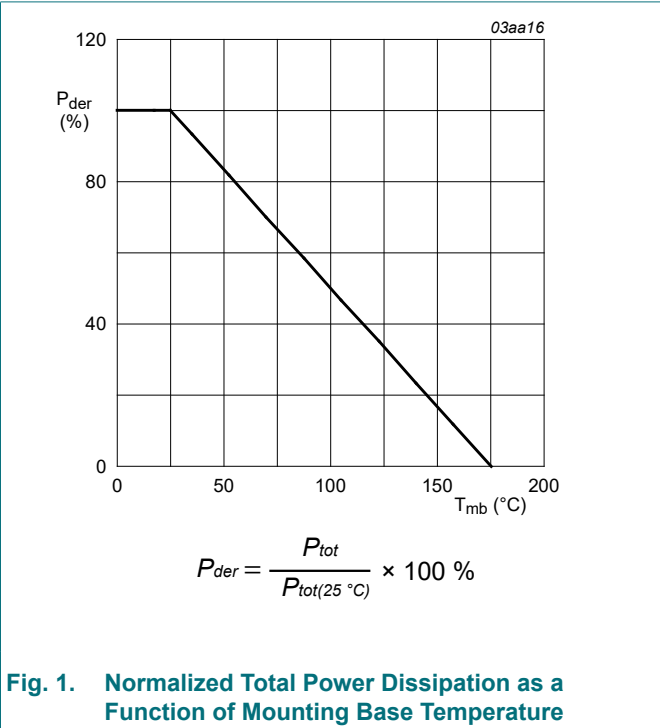
Table 5. Limiting Values

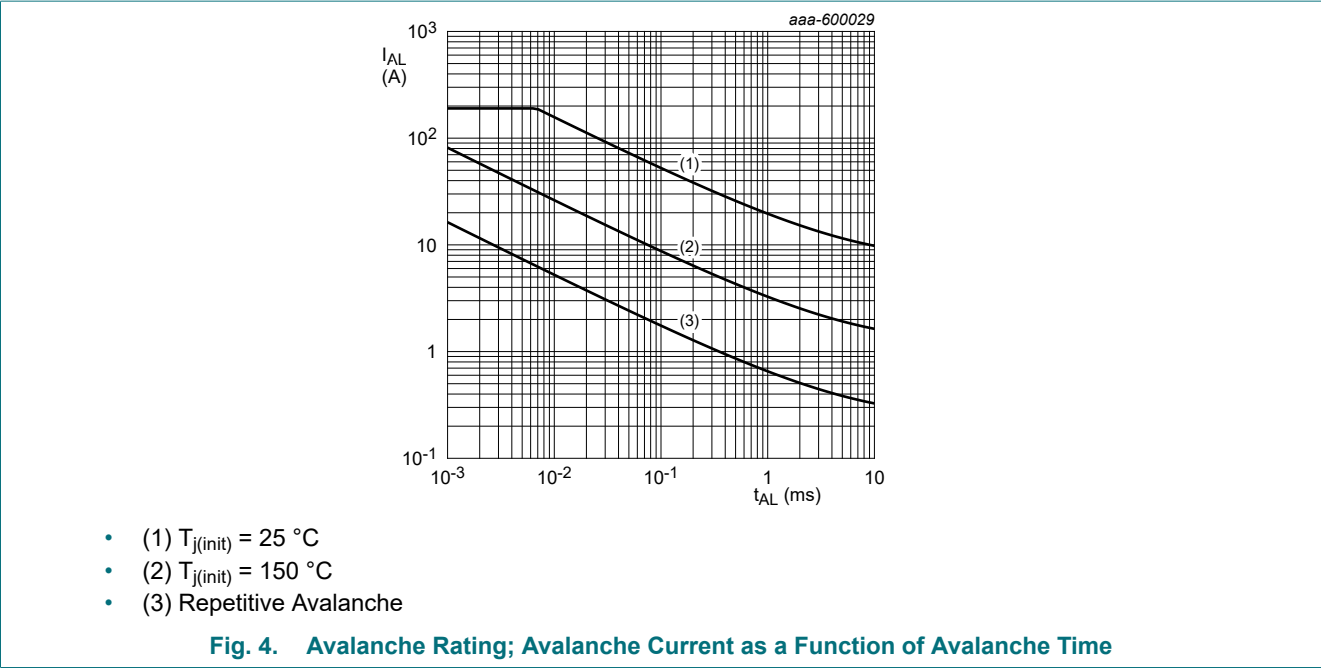
In accordance with the Absolute Maximum Rating System (IEC 60134).  $T_j = 25\text{ °C}$ , unless otherwise specified.

| Symbol             | Parameter               | Conditions                                                                      | Min | Max | Unit |
|--------------------|-------------------------|---------------------------------------------------------------------------------|-----|-----|------|
| $V_{DS}$           | drain-source voltage    | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                      | -   | 40  | V    |
| $V_{GS}$           | gate-source voltage     |                                                                                 | -20 | 20  | V    |
| $P_{tot}$          | total power dissipation | $T_{mb} = 25\text{ °C}$ ; Fig. 1                                                | -   | 273 | W    |
| $I_D$              | drain current           | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 2 [1]                   | -   | 190 | A    |
|                    |                         | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; Fig. 2                      | -   | 190 | A    |
| $I_{DM}$           | peak drain current      | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 3 [1] | -   | 911 | A    |
| $T_{stg}$          | storage temperature     |                                                                                 | -55 | 175 | °C   |
| $T_j$              | junction temperature    |                                                                                 | -55 | 175 | °C   |
| Source-drain Diode |                         |                                                                                 |     |     |      |
| $I_S$              | source current          | $T_{mb} = 25\text{ °C}$                                                         | -   | 190 | A    |
| $I_{SM}$           | peak source current     | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$              | -   | 911 | A    |

| Symbol               | Parameter                                    | Conditions                                                                                                                                                                        | Min | Max | Unit |
|----------------------|----------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|------|
| Avalanche Ruggedness |                                              |                                                                                                                                                                                   |     |     |      |
| $E_{DS(AL)S}$        | non-repetitive drain-source avalanche energy | $I_D = 52\text{ A}$ ; $V_{sup} \leq 40\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; unclamped; Fig. 4 [2] | -   | 136 | mJ   |
| $I_{AS}$             | non-repetitive avalanche current             | $V_{sup} \leq 40\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $R_{GS} = 50\text{ }\Omega$ ; Fig. 4 [3]                                  | -   | 190 | A    |

- [1] Application tests show a continuous current of 190 A. The PCB, the thermal design, and the operating temperature limit the actual current.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.  
Refer to AN10273 for further information.
- [3] Protected by 100% test.



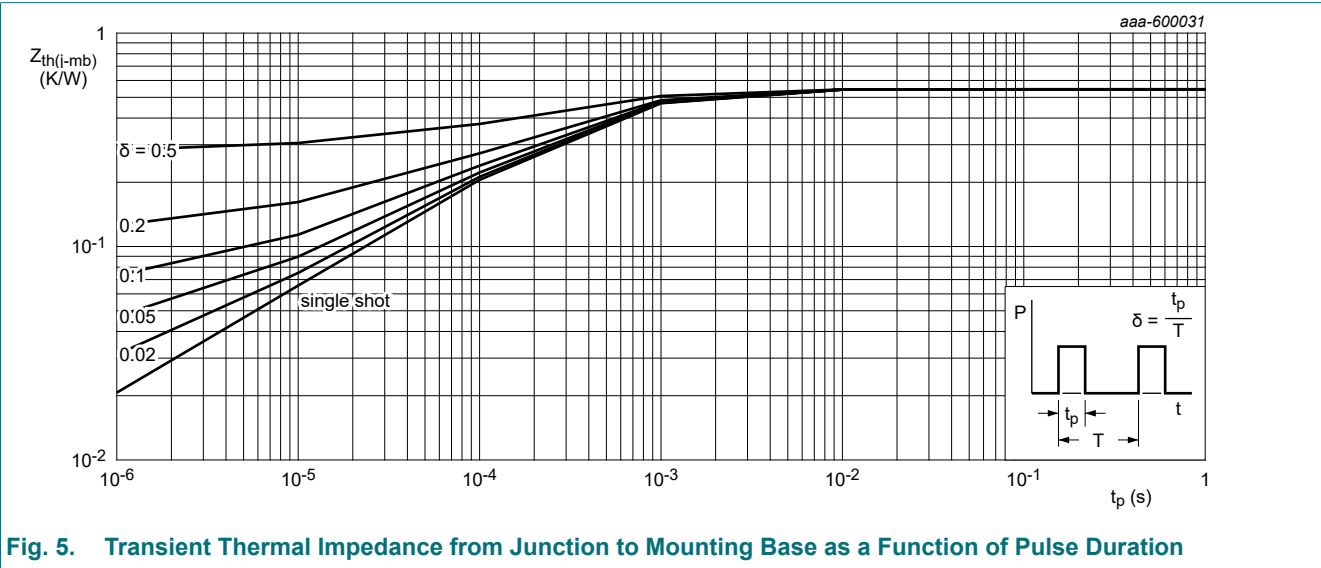


9. Thermal Characteristics

Table 6. Thermal Characteristics

| Symbol         | Parameter                                                  | Conditions             | Min | Typ  | Max  | Unit |
|----------------|------------------------------------------------------------|------------------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base          | <a href="#">Fig. 5</a> | -   | 0.42 | 0.55 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient <sup>[1]</sup> |                        | -   | 24   | -    | K/W  |

[1] Device on 4 layer PCB. Refer to TN00008 for further information.

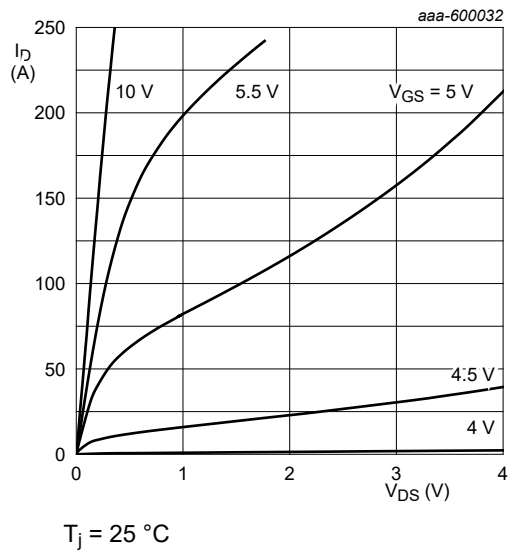


## 10. Characteristics

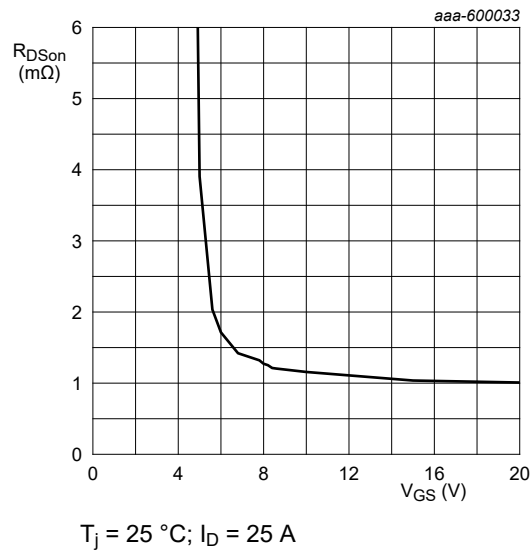
Table 7. Characteristics

| Symbol                  | Parameter                        | Conditions                                                                                                                                                 | Min  | Typ  | Max  | Unit |
|-------------------------|----------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------|------|------|------|------|
| Static Characteristics  |                                  |                                                                                                                                                            |      |      |      |      |
| V <sub>(BR)DSS</sub>    | drain-source breakdown voltage   | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                                                     | 40   | 43   | -    | V    |
|                         |                                  | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -40 °C                                                                                    | -    | 42.5 | -    | V    |
|                         |                                  | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C                                                                                    | 36   | 42.2 | -    | V    |
| V <sub>GS(th)</sub>     | gate-source threshold voltage    | I <sub>D</sub> = 0.3 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a> ; <a href="#">Fig. 9</a>                       | 2    | 3    | 4    | V    |
|                         |                                  | I <sub>D</sub> = 0.3 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <a href="#">Fig. 9</a>                                               | -    | -    | 4.4  | V    |
|                         |                                  | I <sub>D</sub> = 0.3 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <a href="#">Fig. 9</a>                                               | 1    | -    | -    | V    |
| I <sub>DSS</sub>        | drain leakage current            | V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                                                      | -    | 0.05 | 1    | μA   |
|                         |                                  | V <sub>DS</sub> = 16 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C                                                                                     | -    | 3    | 10   | μA   |
|                         |                                  | V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C                                                                                     | -    | 50   | 200  | μA   |
| I <sub>GSS</sub>        | gate leakage current             | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                                                      | -    | 5    | 100  | nA   |
|                         |                                  | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                                                     | -    | 10   | 100  | nA   |
| R <sub>DSon</sub>       | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>                                                             | 0.67 | 1.23 | 1.41 | mΩ   |
|                         |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; <a href="#">Fig. 11</a>                                                            | 1.08 | 1.6  | 2.12 | mΩ   |
|                         |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; <a href="#">Fig. 11</a>                                                            | 1.15 | 1.74 | 2.33 | mΩ   |
|                         |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; <a href="#">Fig. 11</a>                                                            | 1.45 | 2.1  | 2.75 | mΩ   |
| R <sub>G</sub>          | gate resistance                  | f = 1 MHz; T <sub>j</sub> = 25 °C                                                                                                                          | 0.1  | 0.5  | 1.0  | Ω    |
| Dynamic Characteristics |                                  |                                                                                                                                                            |      |      |      |      |
| Q <sub>G(tot)</sub>     | total gate charge                | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>           | -    | 55   | 66   | nC   |
| Q <sub>GS</sub>         | gate-source charge               |                                                                                                                                                            | -    | 15   | 22   | nC   |
| Q <sub>GD</sub>         | gate-drain charge                |                                                                                                                                                            | -    | 12   | 17   | nC   |
| C <sub>iss</sub>        | input capacitance                | V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 14</a>                                                  | -    | 3776 | 5664 | pF   |
| C <sub>oss</sub>        | output capacitance               |                                                                                                                                                            | -    | 1049 | 1574 | pF   |
| C <sub>rss</sub>        | reverse transfer capacitance     |                                                                                                                                                            | -    | 14   | 21   | pF   |
| t <sub>d(on)</sub>      | turn-on delay time               | V <sub>DS</sub> = 32 V; R <sub>L</sub> = 1.3 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C                                  | -    | 20.6 | -    | ns   |
| t <sub>r</sub>          | rise time                        |                                                                                                                                                            | -    | 11.4 | -    | ns   |
| t <sub>d(off)</sub>     | turn-off delay time              |                                                                                                                                                            | -    | 42.7 | -    | ns   |
| t <sub>f</sub>          | fall time                        |                                                                                                                                                            | -    | 11.8 | -    | ns   |
| Source-drain Diode      |                                  |                                                                                                                                                            |      |      |      |      |
| V <sub>SD</sub>         | source-drain voltage             | I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a>                                                              | -    | 0.8  | 1    | V    |
| t <sub>rr</sub>         | reverse recovery time            | I <sub>S</sub> = 25 A; di <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 16</a> [1] | -    | 52.1 | -    | ns   |
| Q <sub>r</sub>          | recovered charge                 |                                                                                                                                                            | -    | 67.7 | -    | nC   |

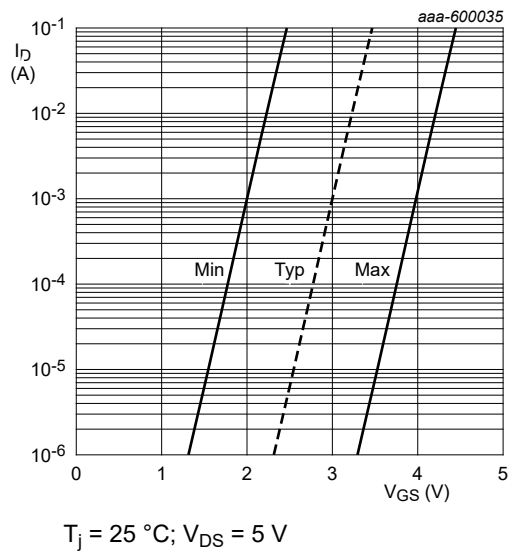
[1] Includes capacitive recovery



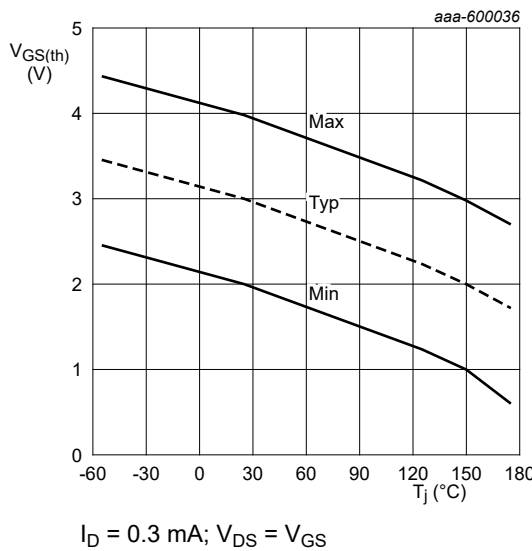
**Fig. 6. Output Characteristics; Drain Current as a Function of Drain-source Voltage; Typical Values**



**Fig. 7. Drain-source On-state Resistance as a Function of Gate-source Voltage; Typical Values**



**Fig. 8. Sub-threshold Drain Current as a Function of Gate-source Voltage**



**Fig. 9. Gate-source Threshold Voltage as a Function of Junction Temperature**

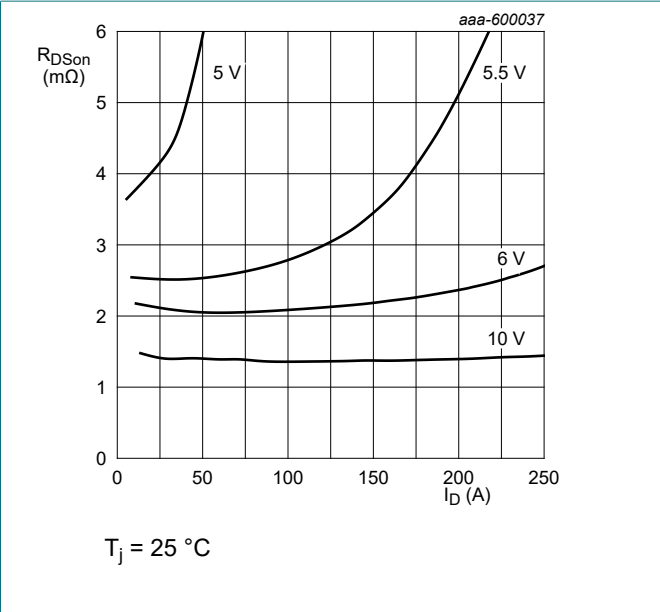


Fig. 10. Drain-source On-state Resistance as a Function of Drain Current; Typical Values

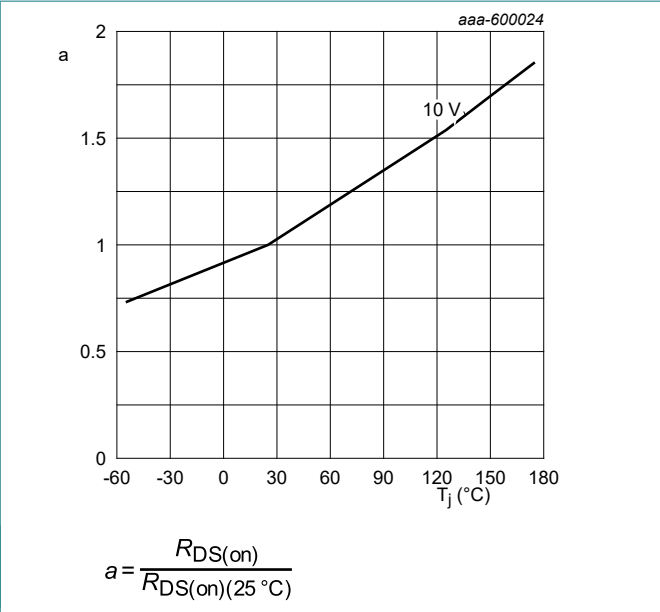


Fig. 11. Normalized Drain-source On-state Resistance Factor as a Function of Junction Temperature

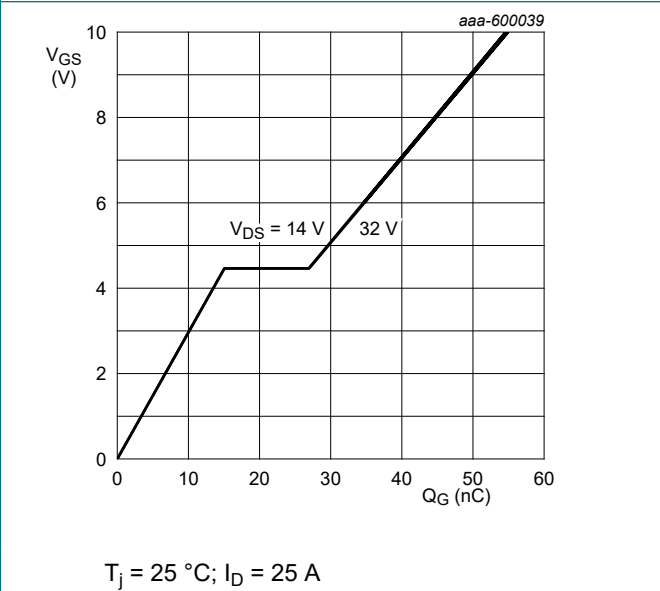


Fig. 12. Gate-source Voltage as a Function of Gate Charge; Typical Values

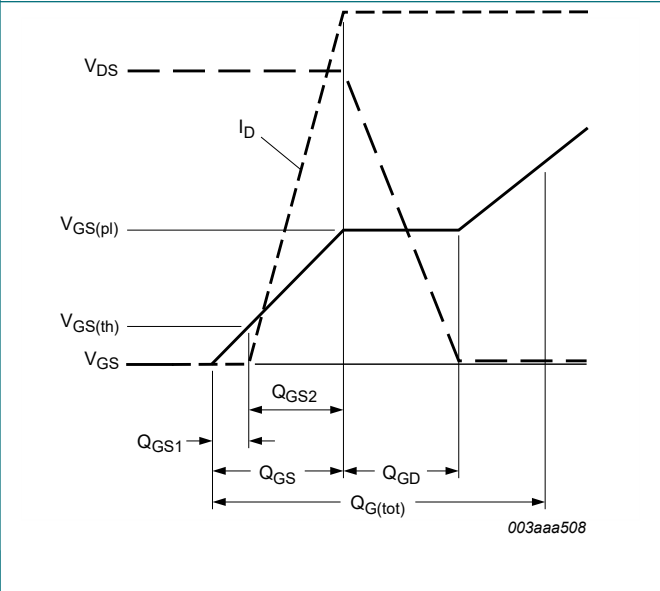


Fig. 13. Gate Charge Waveform Definitions

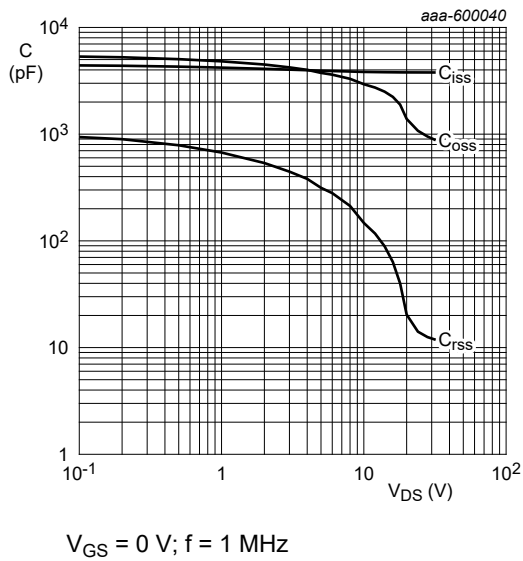


Fig. 14. Input, Output, and Reverse Transfer Capacitances as a Function of Drain-source Voltage; Typical Values

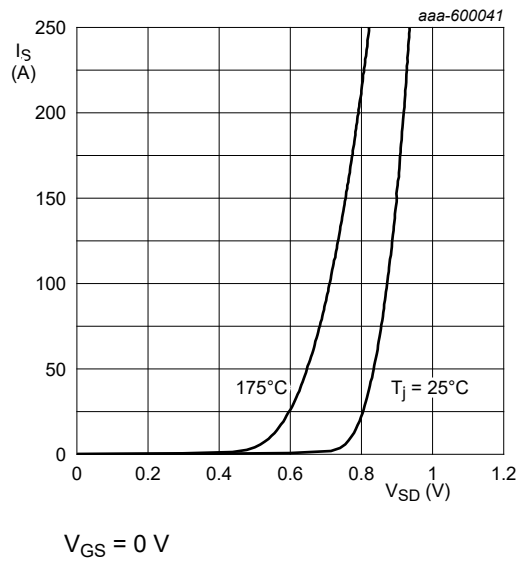


Fig. 15. Source-drain (Diode Forward) Current as a Function of Source-drain (Diode Forward) Voltage; Typical Values

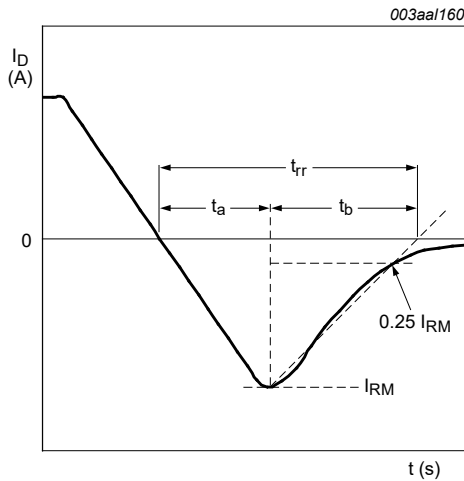


Fig. 16. Reverse Recovery Timing Definition

11. Package Outline

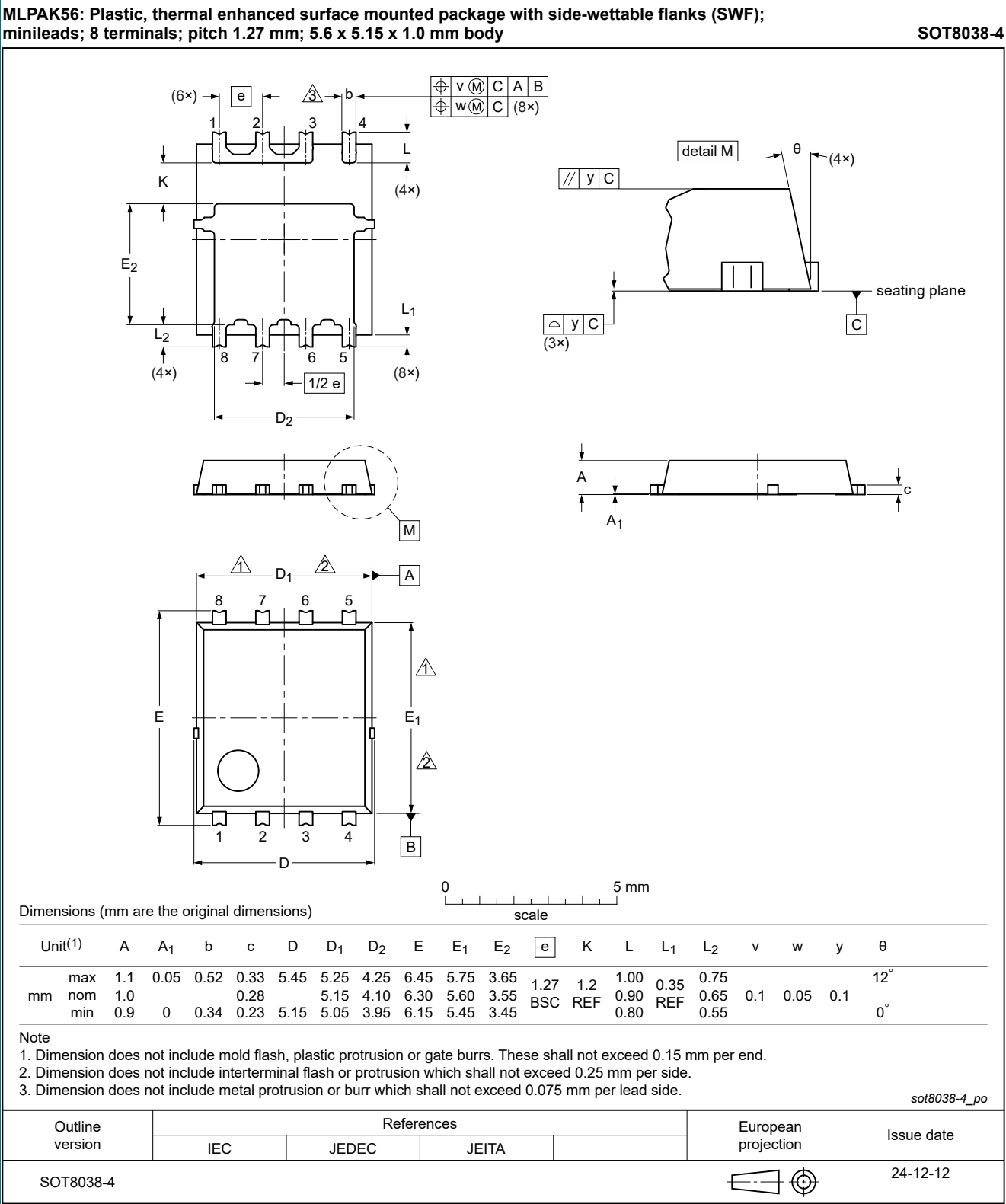


Fig. 17. Package Outline MLPAK56 (SOT8038-4)

12. Soldering

Table 8. Soldering

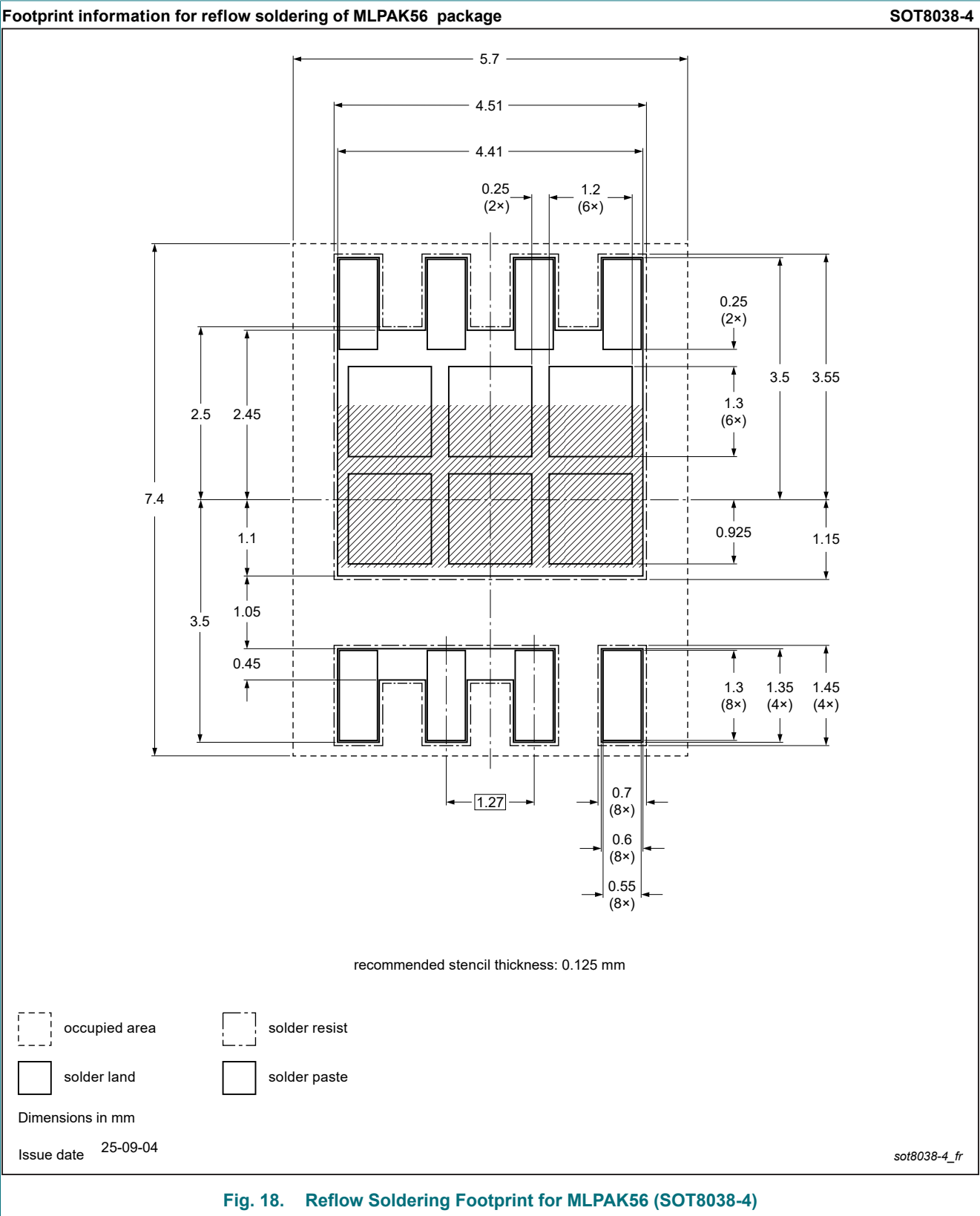


Fig. 18. Reflow Soldering Footprint for MLPAK56 (SOT8038-4)

### 13. Revision History

Table 9. Revision History

| Document ID          | Release Date | Data Sheet Status  | Supersedes |
|----------------------|--------------|--------------------|------------|
| BUKNS1R4-40MYX8 v. 1 | 20260729     | Product data sheet | -          |

## 14. Legal information

### Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

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